

Amendments to the Specification:

Please replace the paragraph bridging from page 10 to page 11 with the following:

In those instances in which the reactor is to be used in an electroplating process, the rotor assembly 45 of head 30 may include one or more cathode contacts that provide electroplating power to the surface of the wafer. In the illustrated embodiment, a cathode contact assembly is shown generally at 90. This cathode contact assembly may be constructed in accordance with the teachings of PCT Application No. PCT/US99/15847, entitled "METHOD AND APPARATUS FOR COPPER PLATING USING ELECTROLESS PLATING AND ELECTROPLATING", filed July 12, 1999 (Attorney Docket No. SEM4492P0571PC; Corporate Docket No. P99-0025PCT). Although the various contact configurations illustrated in that patent application provide electroplating power directly to the side of the wafer that is to be processed, it will be recognized that backside contact may be implemented in lieu of front side contact when the substrate is conductive or other means are provided to electrically connect the backside of the workpiece with the process side thereof. The contact assembly 90 may be operated between an open state that allows the wafer to be placed on the rotor assembly 45, and a closed state that secures the wafer to the rotor assembly and brings the electrically conductive components of the contact assembly 85-90 into electrical engagement with the surface of the wafer that is to be plated.

Please replace the paragraph bridging from page 19 to page 20 with the following:

Although, as noted above, the present invention is suitable for use in a wide range of microelectronic workpiece processes, it is particularly well-suited for use in microelectronic workpiece electroplating. After plating a wafer, the surface of the wafer that has been exposed to the plating solution is wetted with plating solution. The contact assembly and corresponding barrier seal are also wetted at the seal interface with the wafer. This condition is difficult to solve due to conflicting requirements. The

wafer needs to remain wetted until the plating solution can be neutralized by deionized water or another neutralizer. The contact seal, on the other hand, needs the residual solution removed or dried to prevent migration of the plating solution to the sealed area, and ultimately behind it, during product removal. Simply trying drying this residual plating solution is not an option to ~~to~~ the corrosive/oxidizing effect drying has on the plated film. Such problems are addressed by rinsing the wafer and seal interface before the wafer is removed from then reactor. Also, it has been found to be desirable to occasionally rinse the seal and electrical contact in the absence of a wafer to assist in preventing a buildup of copper salts.